



80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	7mΩ @ V _{GS} = 10V	68A
80V	10.5mΩ @ V _{GS} = 6V	56A

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

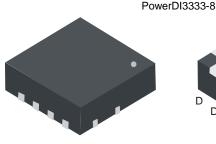
Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- Low Rds(ON) Ensures On-State Losses are Minimized
- Excellent Q_{gd} × R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH8008SFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

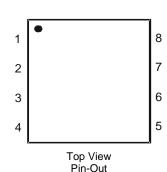
https://www.diodes.com/quality/product-definitions/

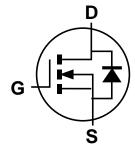
Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)









Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH8008SFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMTH8008SFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



HZ8 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	80	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ID	68 48	А
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		ID	17 12	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	68	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ірм	272	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle =	I _{SM}	272	Α	
Avalanche Current, L = 1mH (Note 8)	las	18.7	Α	
Avalanche Energy, L = 1mH (Note 8)	Eas	174.85	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	125	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	46	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	Pp	50	W
Thermal Resistance, Junction to Case (Note 7)		R _θ JC	3.0	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

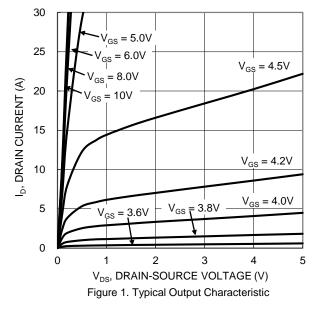
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	80	-	_	V	$V_{GS} = 0V$, $I_{D} = 1mA$	
Zero Gate Voltage Drain Current	IDSS	-	-	1	μΑ	V _{DS} = 64V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(TH)	2	-	4	V	V _{DS} = V _{GS} , I _D = 1mA	
Static Drain-Source On-Resistance		-	5.0	7	mΩ	Vgs = 10V, ID = 14A	
Static Drain-Source On-Resistance	RDS(ON)	_	7.1	10.5		V _G S = 6V, I _D = 12A	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	V _{GS} = 0V, I _S = 14A	
DYNAMIC CHARACTERISTICS (Note 10)	ŭ 1 1 1 1 1 1 1 1						
Input Capacitance	Ciss		1945			V _{DS} = 40V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	-	750	_	pF		
Reverse Transfer Capacitance	Crss	-	45.8	_			
Gate Resistance	Rg	_	1.8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 5V)	Qg	-	18.4	_	nC Vps = 40V lp = 14A		
Total Gate Charge (V _{GS} = 10V)	Qg	_	31.7	_			
Gate-Source Charge	Q _{gs}	_	8.3	_	nc	$V_{DS} = 40V, I_{D} = 14A$	
Gate-Drain Charge	Q_{gd}	-	8.6	_			
Turn-On Delay Time	tD(ON)	_	9.2	_		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 14A, R_{G} = 6\Omega$	
Turn-On Rise Time	t _R	_	11.8	_	20		
Turn-Off Delay Time	tD(OFF)	_	27.0	_	ns		
Turn-Off Fall Time	tF		17.3	_			
Body Diode Reverse Recovery Time	trr		40.6	_	ns	1 440 41/44 4000///-	
Body Diode Reverse Recovery Charge	Q _{RR}	_	50.9	_	nC	$I_S = 14A$, di/dt = 100A/ μ s	

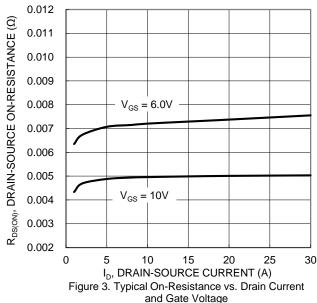
Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.









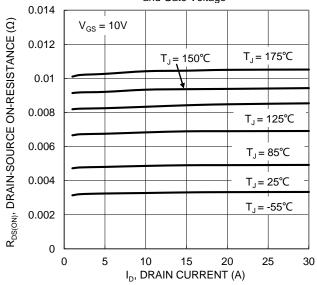


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

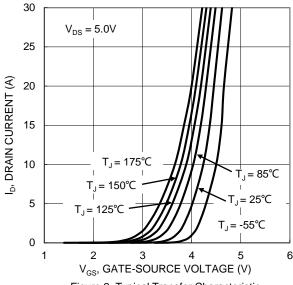
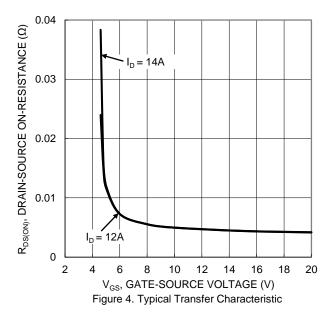


Figure 2. Typical Transfer Characteristic



2.4 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 2.2 2 $V_{GS} = 10V, I_D = 14A$ 1.8 1.6 1.4 1.2 1 $V_{GS} = 6V, I_{D} = 12A$ 0.8 0.6 0.4 150 175 0 -50 25 50 75 100 125 T_J, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature





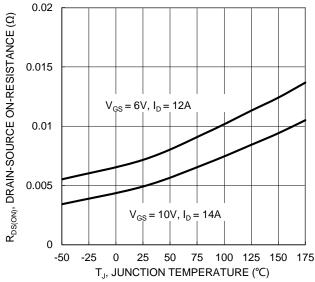


Figure 7. On-Resistance Variation with Temperature

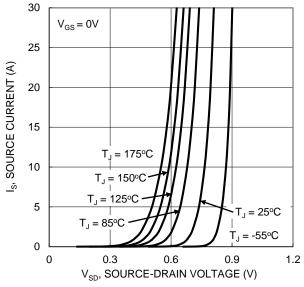


Figure 9. Diode Forward Voltage vs. Current

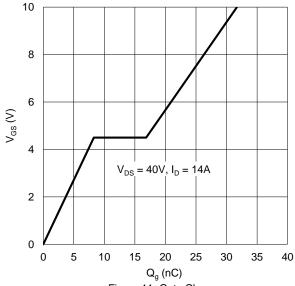


Figure 11. Gate Charge

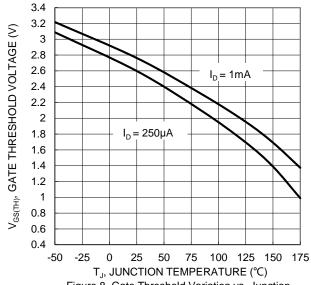
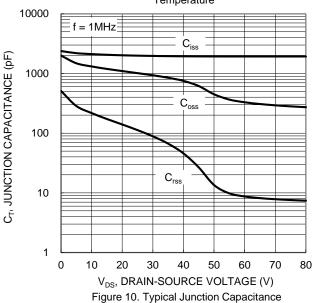


Figure 8. Gate Threshold Variation vs. Junction Temperature



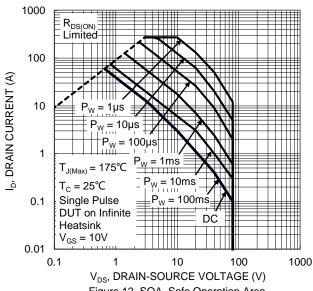


Figure 12. SOA, Safe Operation Area



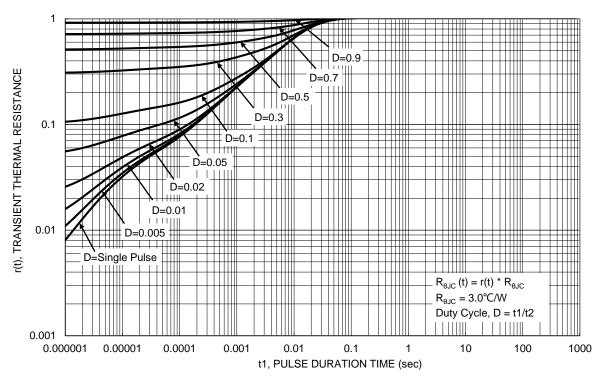


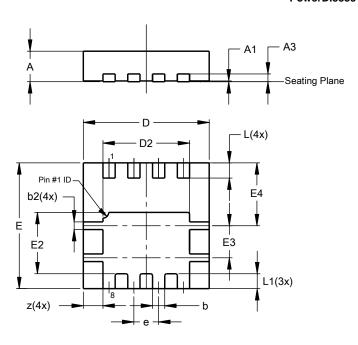
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

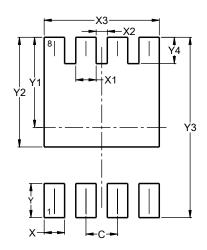


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	-	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
Χ	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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